

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (Use several sheets if necessary)			Attorney Docket No.: 8074-1061	Application No. 11/541,833 NEW NATIONAL PHASE		
			Applicant: Yasuhiro OKAMOTO et al.	Filing Date: July 7, 2005	Group Art Unit:	
U.S. PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Name	Class	Subclass	
					Filing date (if appropriate)	
FOREIGN PATENT DOCUMENTS						
Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation
/VM/	JP 2000-286428	10/13/2000	JAPAN			Yes
	JP 11-176839	7/2/1999	JAPAN			No
	JP 2002-359256	12/13/2002	JAPAN			
	JP 2001-189324	7/10/2001	JAPAN			
	JP 2002-222860	8/9/2002	JAPAN			
/VM/	JP 2000-003919	1/7/2000	JAPAN			
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)						
/VM/	U. K. MISHRA et al., "AlGaN/GaN HEMTs-An Overview of Device Operation and Applications", Proceedings of the IEEE, Vol. 90, No. 6, June 2002					
/VM/	J. LI et al., "High breakdown voltage GaN HFET with field plate", ELECTRONICS LETTERS, 1 st February 2001, Vol. 37, No. 3					
/VM/	Y. ANDO et al., "A 110-W AlGaN/GaN HETEROJUNCTION FET ON THINNED SAPPHIRE SUBSTRATE"					
EXAMINER: Victor Mandala/			DATE CONSIDERED			
						03/27/2007
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* English language abstract provided for the Examiner's convenience